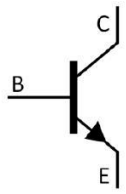
TO-220 NPN Silicon NPN transistor in a TO-220 Plastic Package.

BD912

High V_{CEO}, larger I_C, complement to BD912.

Use in power linear and switching applications.



PIN1 Base PIN 2 Collector PIN 3 Emitter

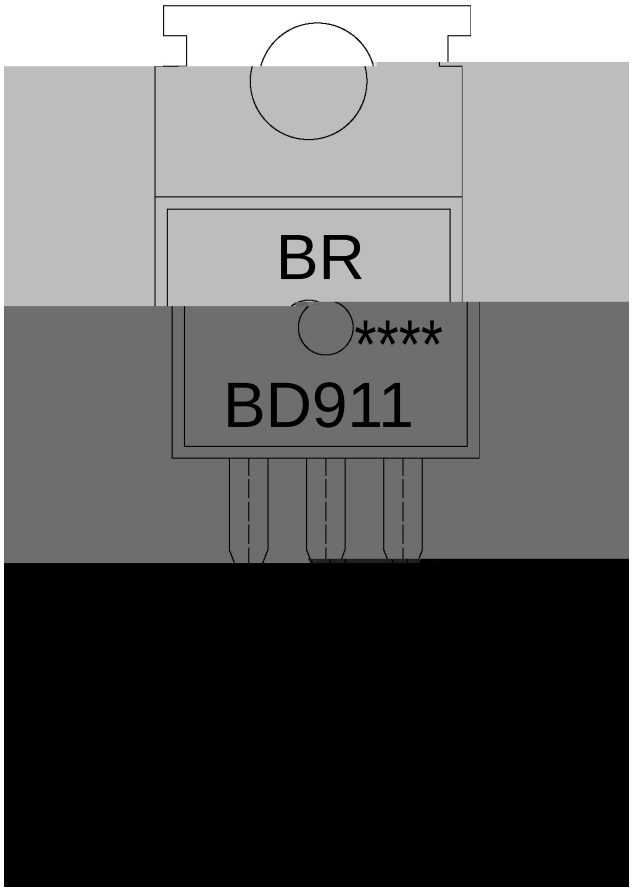
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	100	V
Collector to Emitter Voltage	V_{CEO}	100	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	15	A
Base Current – Continuous	I_B	5.0	A
Collector Power Dissipation	$P_C(T_C=25$)	90	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	100			V
Collector Cut-Off Current	$I_{CBO(1)}$	V_{CB}=100V I_E=0			0.5	mA
	$I_{CBO(2)}$	V_{CB}=100V I_E=0 T_C=150			5.0	mA
Collector Cut-Off Current	I_{CEO}	V_{CE}=50V I_B=0			1.0	mA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			1.0	mA
DC Current Gain	$h_{FE(1)}$	V_{CE}=4.0V I_C=0.5A	40		250	
	$h_{FE(2)}$	V_{CE}=4.0V I_C=5.0A	15		150	
	$h_{FE(3)}$	V_{CE}=4.0V I_C=10A	5			

Collector to Emitter Saturation


A
C
B
3°
a
b1
C1
a1
E1
3%



BR

BD911

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Note:

BR:	Company Code
BD911:	Product Type.
****:	Lot No. Code, code change with Lot No.